



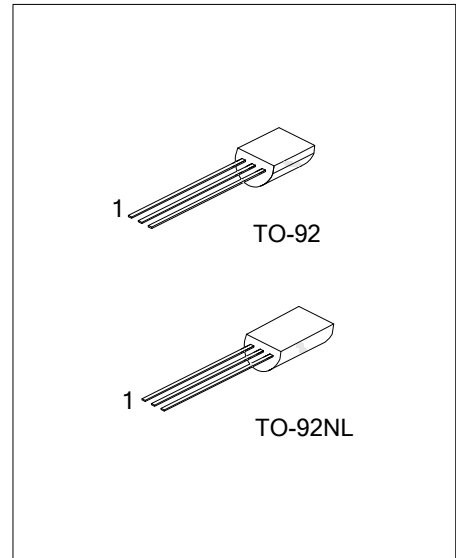
2SB562

PN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

■ FEATURES

- * Low frequency power amplifier
- * Complement to 2SD468



■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SB562L-x-T92-B	2SB562G-x-T92-B	TO-92	E	C	B	Tape Box
2SB562L-x-T92-K	2SB562G-x-T92-K	TO-92	E	C	B	Bulk
2SB562L-x-T9N-B	2SB562G-x-T9N-B	TO-92NL	E	C	B	Tape Box
2SB562L-x-T9N-K	2SB562G-x-T9N-K	TO-92NL	E	C	B	Bulk

<p>2SB562L-x-T92-R</p> <p>(1) Packing Type (2) Package Type (3) Rank (4) Lead Plating</p>	<p>(1) B: Tape Box, K: Bulk (2) T92: TO-92, T9N: TO-92NL (3) x: refer to Classification of h_{FE} (4) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATING ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-25	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1	A
Collector Peak Current	$I_C(\text{peak})$	-1.5	A
Collector Power Dissipation	P_C	0.9	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified)

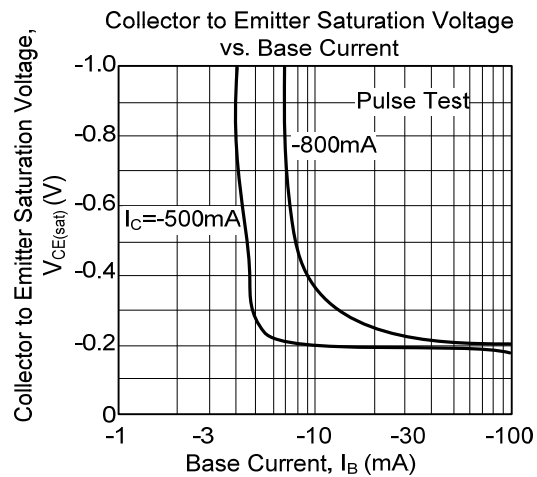
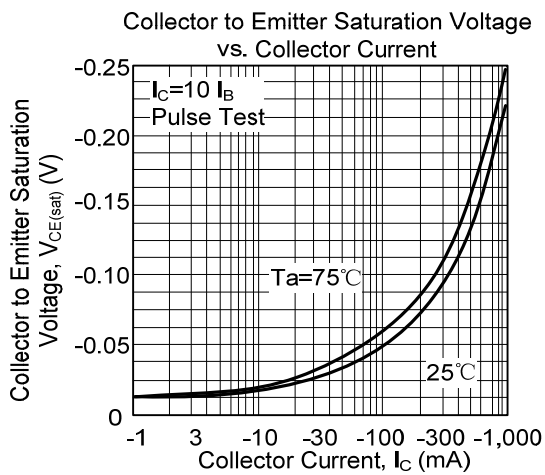
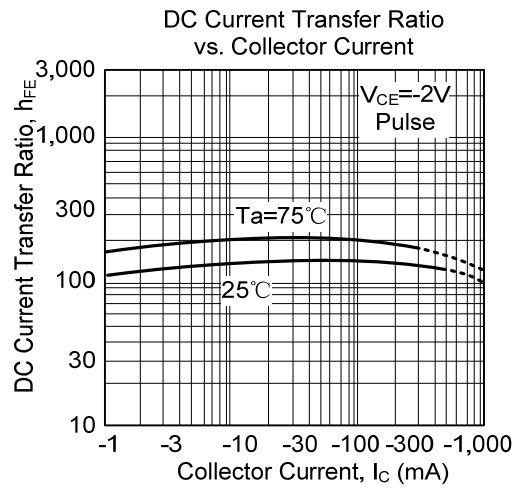
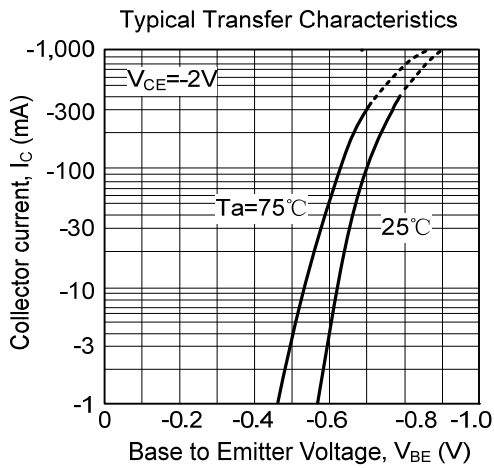
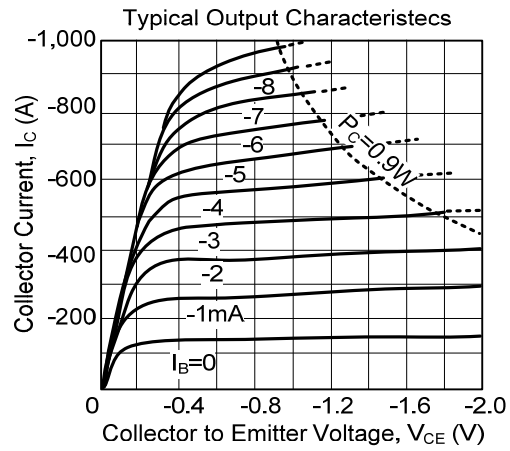
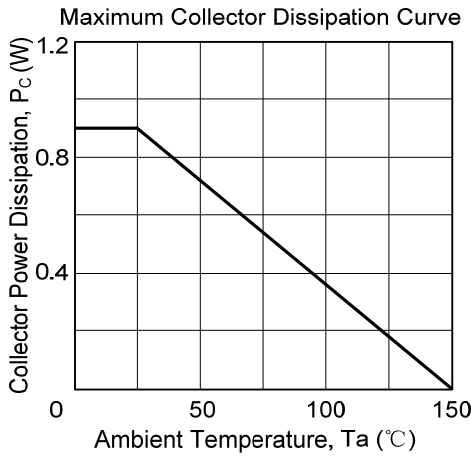
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}$, $I_E=0$	-25			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $R_{BE}=\infty$	-20			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}$, $I_C=0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-20\text{V}$, $I_E=0$			-1	μA
DC Current Transfer Ratio	h_{FE}	$V_{CE}=-2\text{V}$, $I_C=-0.5\text{A}$ (note)	85		240	
Collector to Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C=-0.8\text{A}$, $I_B=-0.08\text{A}$ (note)		-0.2	-0.5	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-2\text{V}$, $I_C=-0.5\text{A}$ (note)		-0.8	-1.0	V
Gain Bandwidth Product	f_T	$V_{CE}=-2\text{V}$, $I_C=-0.5\text{A}$ (note)		350		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$		38		pF

Note 1: Pulse test

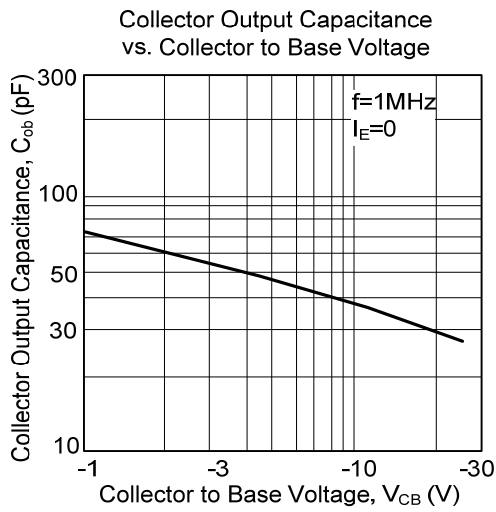
■ CLASSIFICATION OF h_{FE}

RANK	B	C
RANGE	85 - 170	120 - 240

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS



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